

Feature

- Precision MEMS process
- High performance, shielded, Micro-cavity structure
- Silicon substrate, 50Ω CPW output
- Au wire bonding, for MCM applications

Environmental Specifications

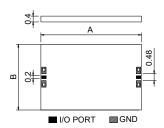
Operating Temperature	-55℃~+85℃	
Storage Temperature	-55°C∼+125°C	
Max. Input Power	35dBm	

Electrical Specifications(T_A=+25°C)

Parameter	Min.	Тур.	Max.	Unit
Center Freq. (f₀)	-	15.0	ı	GHz
Pass Band	14.0	-	16.0	GHz
Ripple in Pass band	-	-	1	dB
Insertion Loss @ f₀	-	-	2.0	dB
Return Loss	12	-	ı	dB
≥30@13.1&16.8GHz				dB
Out of band	≥40@12	dB		
Attenuation	≥60@DC~12GHz			dB
	≥50@18~28GHz			dB
Group Delay Variation	≤0.5@14.0~16.0 GHz			
Linear Phase	≤±7@14.0~16.0 GHz			

S2P file name: SiMS15_2R1-8D2.s2p

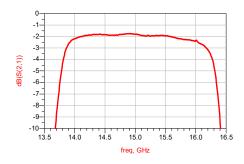
Outline Drawing



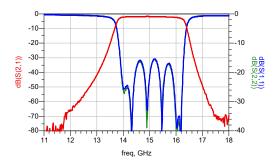
Symbol	Value (mm)			
Symbol	Min.	Nominal	Max.	
А	8.9	-	9.0	
В	3.9	-	3.2	

Typical Test Curves

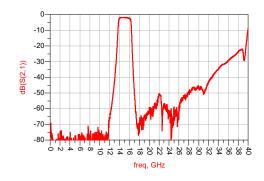
Insertion Loss VS Frequency (T_A=25°C)



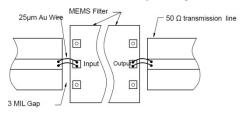
Insertion Loss & Return Loss VS Frequency (T_A=25°C)



Broadband Insertion Loss VS Frequency (T_A=25°C)

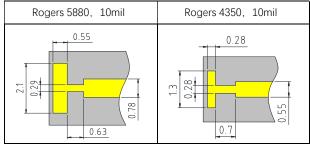


Recommended Assembly Diagrams



Application Notes:

- 1. The chip is back-metalized and can be die mounted with AuSn eutectic performs or with electrically conductive epoxy (for example ME8456).
- 2. The die should be assembled on carriers like Kovar or Mu-Cu which have same Coefficient of thermal expansion. (2.9ppm/ $^{\circ}$ C) with Silicon, thickness 0.2mm max.
- 3. Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.
- 4. Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.
- 5. Recommended to use T structure as below for bonding.



6. If you have any questions, please contact us.